

BUK9Y3R0-40E

N-channel 40 V 3.0 m Ω logic level MOSFET in LFPAK56 11 November 2014

Product data sheet

General description 1.

Logic level N-channel MOSFET in LFPAK56 (Power SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

Features and benefits 2.

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with V_{GS(th)} rating of greater than 0.5 V at 175 °C

Applications

- 12 V Automotive systems
- Motors, lighting and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	40	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	-	100	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	194	W
Static characte	eristics						,
R _{DSon}	drain-source on-state resistance	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$		-	2.47	3	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	V _{GS} = 5 V; I _D = 25 A; V _{DS} = 32 V; Fig. 13; Fig. 14		-	10.7	-	nC

^[1] Continuous current is limited by package.



N-channel 40 V 3.0 m Ω logic level MOSFET in LFPAK56

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	[q]	G
4	G	gate	و ق ق ق	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BUK9Y3R0-40E	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669		

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK9Y3R0-40E	93E040

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	40	V
V_{DGR}	drain-gate voltage	R_{GS} = 20 k Ω		-	40	V
V_{GS}	gate-source voltage	T _j ≤ 175 °C; DC		-10	10	V
		T _j ≤ 175 °C; Pulsed	[1][2]	-15	15	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	194	W
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 5 V; <u>Fig. 2</u>	<u>[3]</u>	-	100	Α
		$T_{mb} = 100 ^{\circ}\text{C}; V_{GS} = 5 \text{V}; \underline{\text{Fig. 2}}$	[3]	-	100	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; Fig. 3		-	718	Α

BUK9Y3R0-40E

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N-channel 40 V 3.0 mΩ logic level MOSFET in LFPAK56

Symbol	Parameter	Conditions		Min	Max	Unit
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drain diode						
I _S	source current	T _{mb} = 25 °C	[3]	-	100	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	718	Α
Avalanche ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 100 A; $V_{sup} \le 40$ V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped; $Fig. 4$	[4][5]	-	193.8	mJ

- Accumulated pulse duration up to 50 hours delivers zero defect ppm Significantly longer life times are achieved by lowering $\rm T_j$ and or $\rm V_{GS}$
- [2]
- Continuous current is limited by package. [3]
- Single-pulse avalanche rating limited by maximum junction temperature of 175 °C. [4]
- Refer to application note AN10273 for further information.

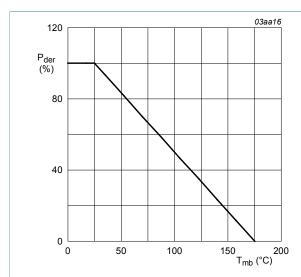
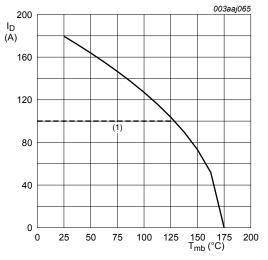


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$



(1) Capped at 100A due to package

Fig. 2. Continuous drain current as a function of mounting base temperature

$$V_{GS} \ge 5V$$

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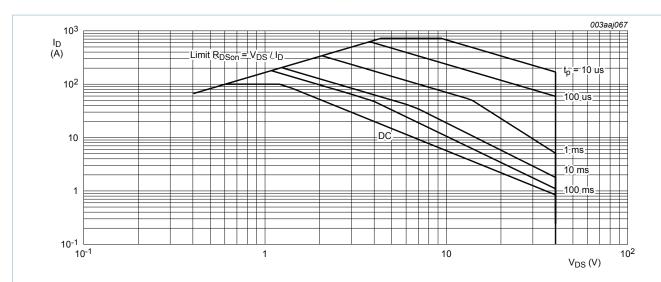
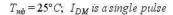


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



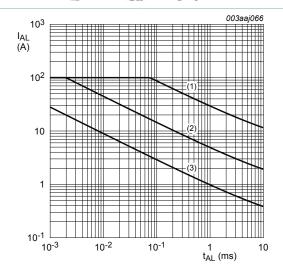


Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

(1) $T_{j \ (int)} = 25^{\circ}C$; (2) $T_{j \ (int)} = 150^{\circ}C$; (3) Repetitive Avalanche

9. Thermal characteristics

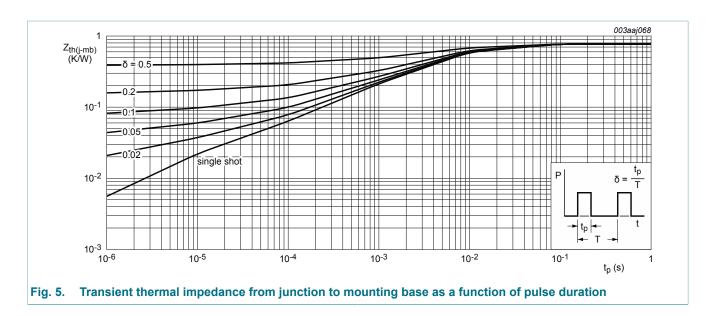
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	_	0.77	K/W

BUK9Y3R0-40E

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N-channel 40 V 3.0 m Ω logic level MOSFET in LFPAK56



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics			'		
V _{(BR)DSS}	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	40	-	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	36	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 9; Fig. 10	1.4	1.7	2.1	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9	-	-	2.45	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 175 °C; Fig. 9	0.5	-	-	V
I _{DSS}	drain leakage current	V _{DS} = 40 V; V _{GS} = 0 V; T _j = 25 °C	-	0.13	10	μA
		V _{DS} = 40 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; <u>Fig. 11</u>	-	2.47	3	mΩ
	resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11	-	1.98	2.5	mΩ
		V _{GS} = 5 V; I _D = 25 A; T _j = 175 °C; Fig. 12; Fig. 11	-	-	6	mΩ
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 32 V; V _{GS} = 5 V;	-	35.5	-	nC
Q_{GS}	gate-source charge	Fig. 13; Fig. 14	-	11.7	-	nC

BUK9Y3R0-40E

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N-channel 40 V 3.0 m Ω logic level MOSFET in LFPAK56

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Q_{GD}	gate-drain charge			-	10.7	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz;		-	4471	5962	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>		-	563	676	pF
C _{rss}	reverse transfer capacitance			-	251	344	pF
t _{d(on)}	turn-on delay time	V_{DS} = 30 V; R_L = 1.2 Ω ; V_{GS} = 5 V;		-	24	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$		-	44	-	ns
t _{d(off)}	turn-off delay time			-	53	-	ns
t _f	fall time			-	34	-	ns
Source-dra	ain diode						
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; Fig. 16		-	0.81	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$		-	30	-	ns
Q _r	recovered charge	V _{DS} = 25 V		-	25	-	nC

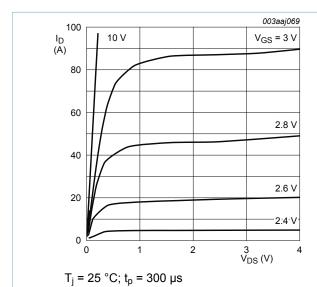


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

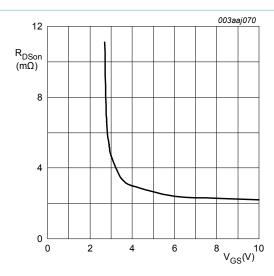


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25^{\circ}C; \ I_D = 25A$$

6/13

N-channel 40 V 3.0 m Ω logic level MOSFET in LFPAK56

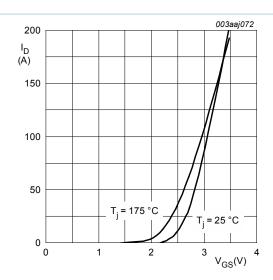


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values



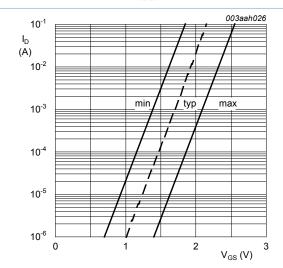


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25^{\circ}C; \ V_{DS} = 5V$$

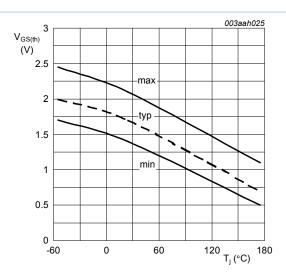
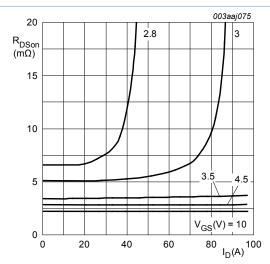


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1$$
 mA; $V_{DS} = V_{GS}$



 $T_i = 25 \, ^{\circ}C; t_p = 300 \, \mu s$

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

N-channel 40 V 3.0 m Ω logic level MOSFET in LFPAK56

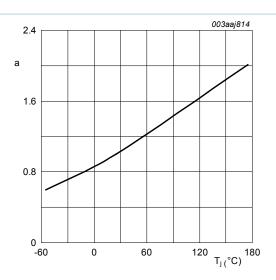


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon (25^{\circ}C)}}$$

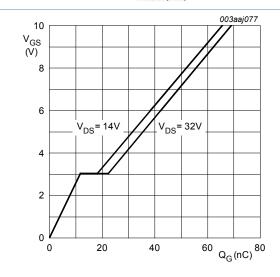


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^{\circ}C; I_D = 25A$$

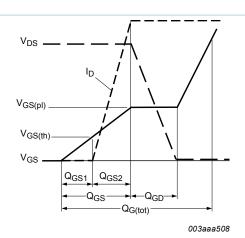


Fig. 13. Gate charge waveform definitions

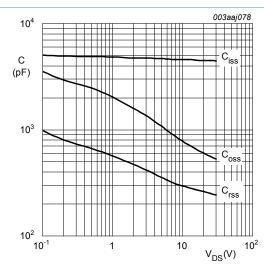


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = \mathbf{0}V; \ f = \mathbf{1}MHz$$

N-channel 40 V 3.0 m Ω logic level MOSFET in LFPAK56

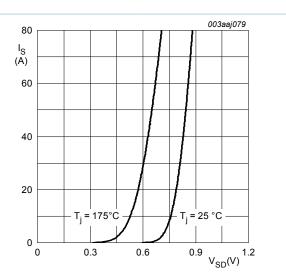


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0V$$

11. Package outline

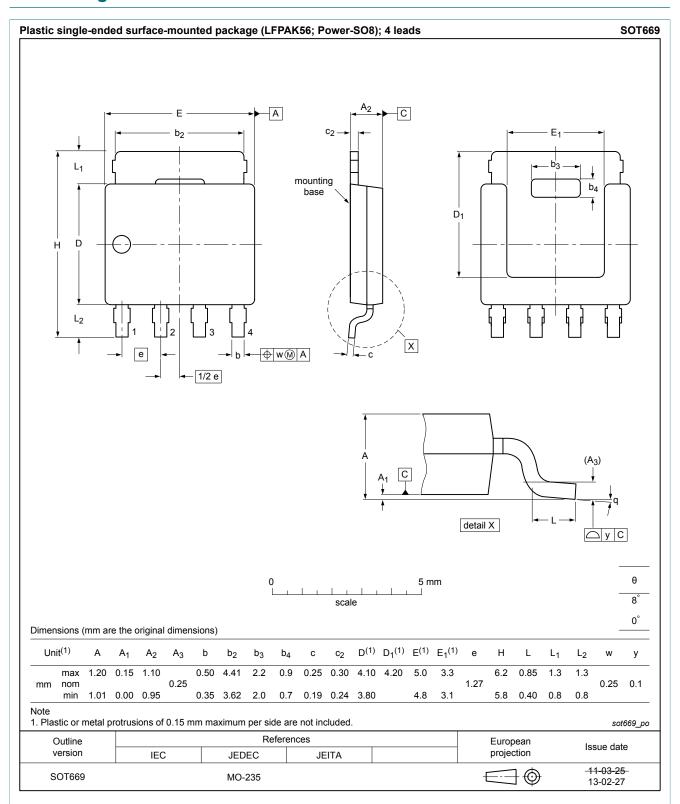


Fig. 17. Package outline LFPAK56; Power-SO8 (SOT669)

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N-channel 40 V 3.0 m Ω logic level MOSFET in LFPAK56

13. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	2
9	Thermal characteristics	4
10	Characteristics	5
11	Package outline	10
12	Legal information	11
12.1	Data sheet status	11
12.2	Definitions	11
12.3	Disclaimers	11
12.4	Trademarks	12

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